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		FORM PTO	0-1449	Atty. Docket No.			ln. No.	
LIST	OF	DOCUMENTS C	ITED BY A	XA-9593			1031117	
				Applicant				
_				Takashi KOBAYASHI et al.				
				Filing Date		Gro	Group	
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me	AL	11-220044	8/10/99	Japan /			_	abstract
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•		OTHER	(including aut	hor, title, da	te, pertinent p	ages, etc.)	
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pt _	AS	Naruke, K. et Gate on its S	al., "A Ne	w Flash-Eras	e EEPROM Ce	ll with a	a Sidew	all Select-
ho		Devices Meeti			a. Digest	or ince	LIACION	ar Election
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